

Description

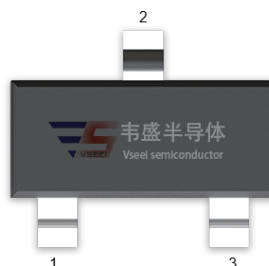
The VSM0102B uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

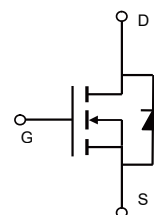
- $V_{DS} = 100V, I_D = 1.8A$
 $R_{DS(ON)} < 680m\Omega @ V_{GS}=10V$ (Typ:530m Ω)
 $R_{DS(ON)} < 700m\Omega @ V_{GS}=4.5V$ (Typ:580m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



SOT-23



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM0102B	VSM0102B-S2	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	1.8	A
Drain Current-Pulsed (Note 1)	I_{DM}	7.2	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^{\circ}C/W$
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Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	V

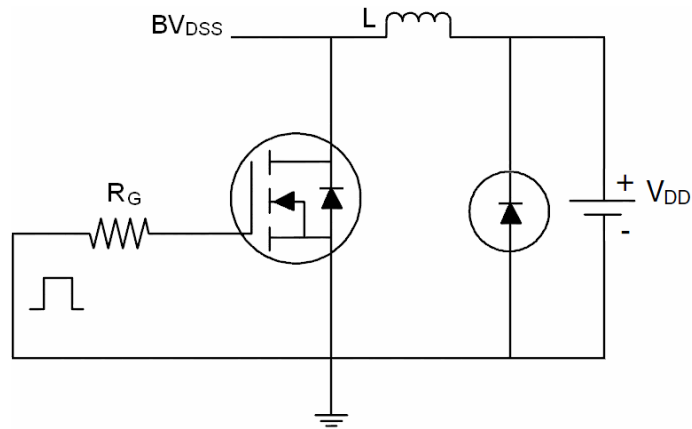
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =1A	-	530	680	mΩ
		V _{GS} =4.5V, I _D =1A	-	580	700	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =1A	1	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	164.6	-	PF
Output Capacitance	C _{oss}		-	11.5	-	PF
Reverse Transfer Capacitance	C _{rss}		-	6	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, R _L =30Ω V _{GS} =10V, R _G =2.5Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	12	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =1A, V _{GS} =10V	-	8.3		nC
Gate-Source Charge	Q _{gs}		-	1.7	-	nC
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	1.8	A

Notes:

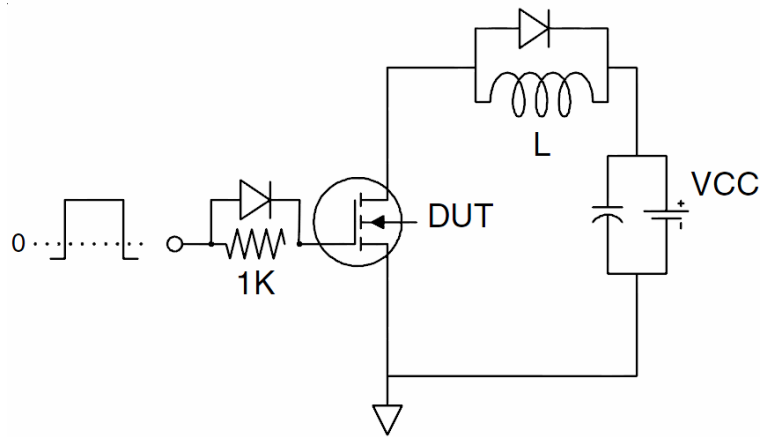
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

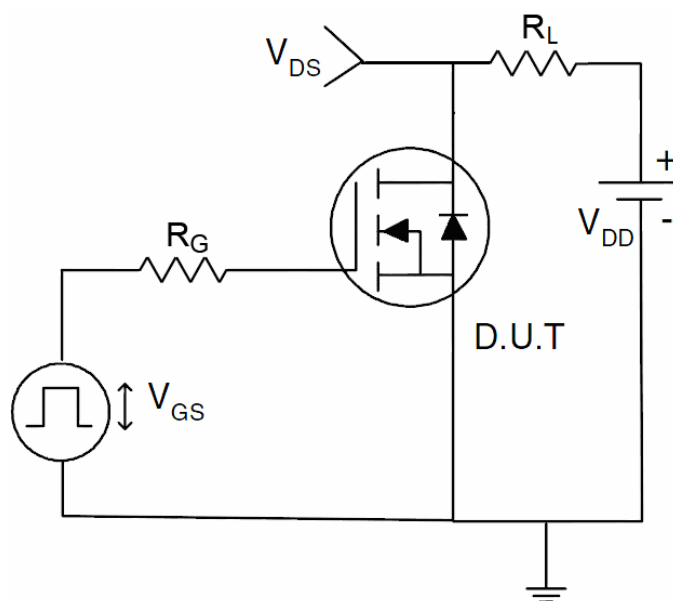
1) E_{AS} test circuit



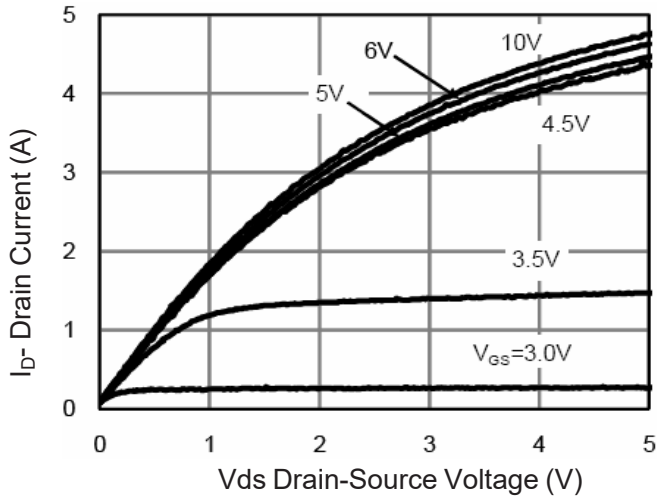
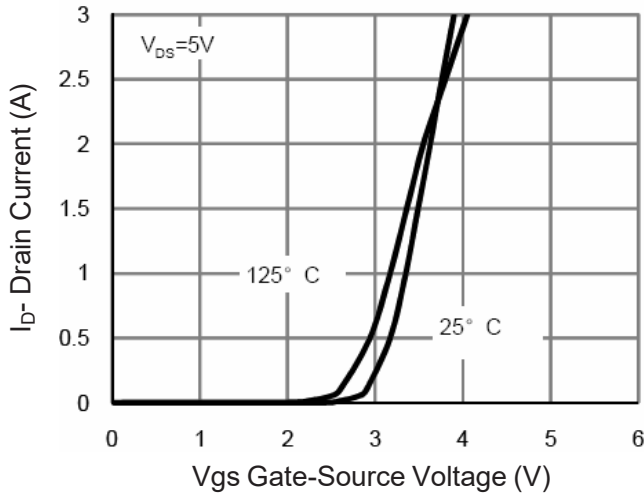
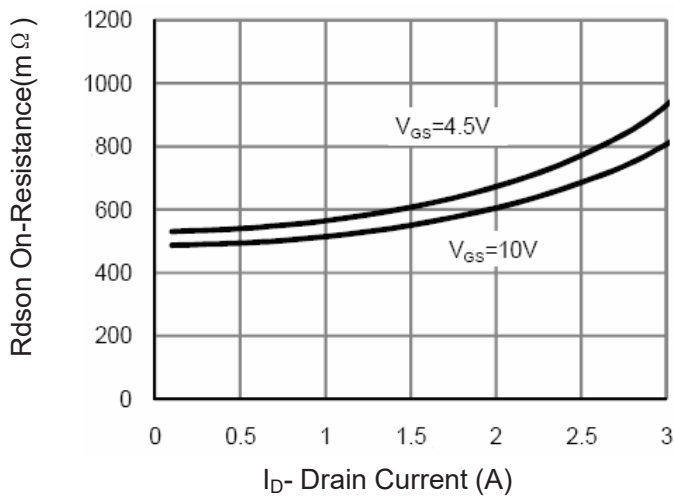
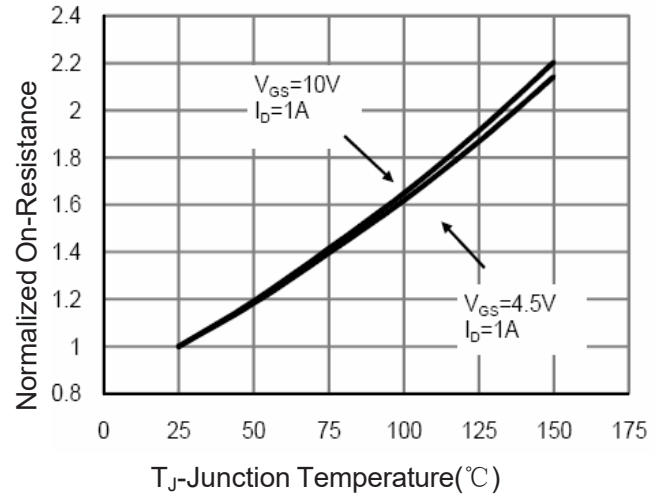
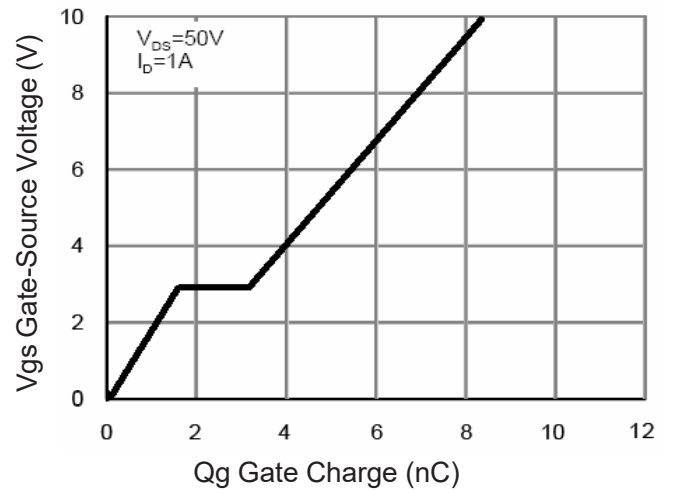
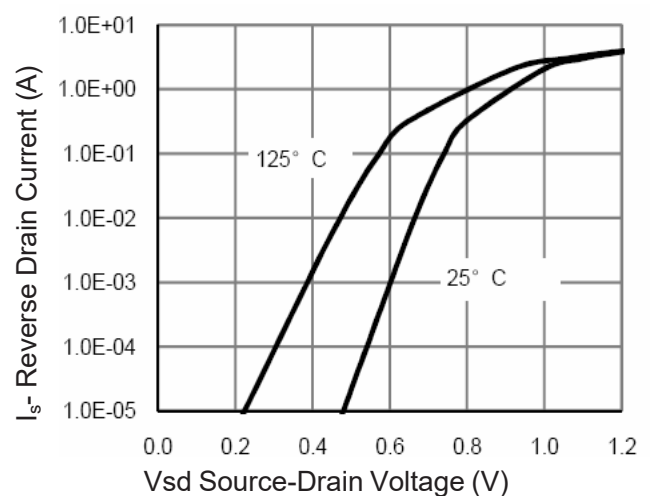
2) Gate charge test circuit

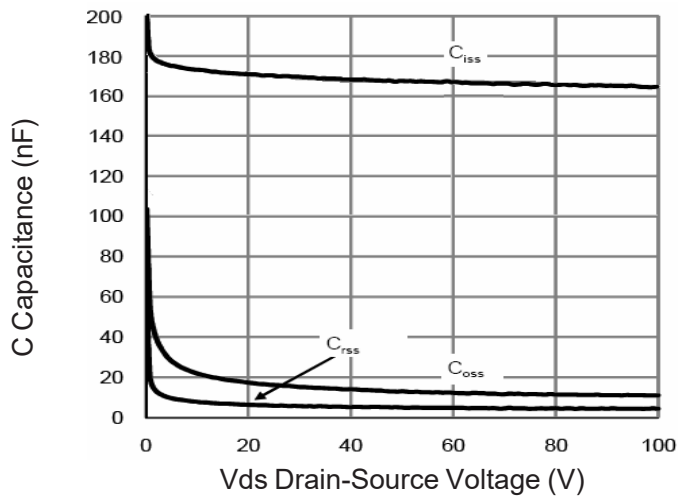
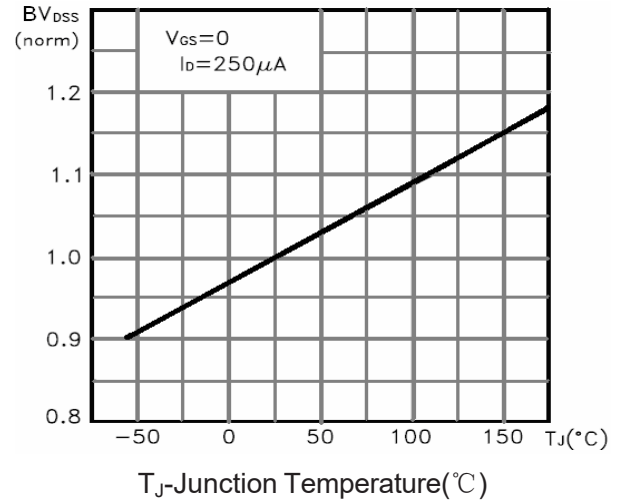
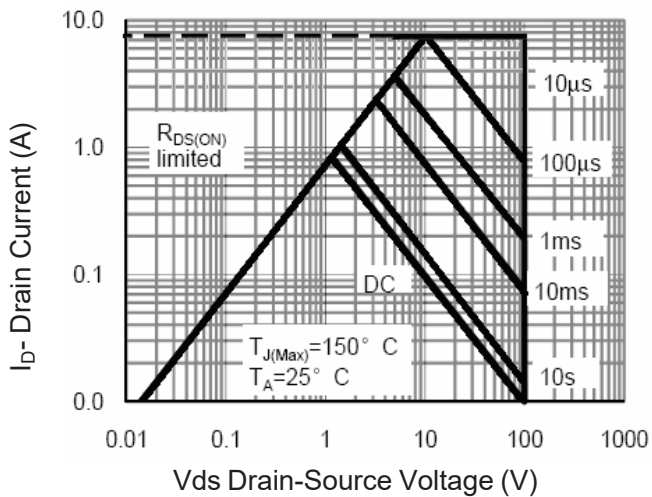
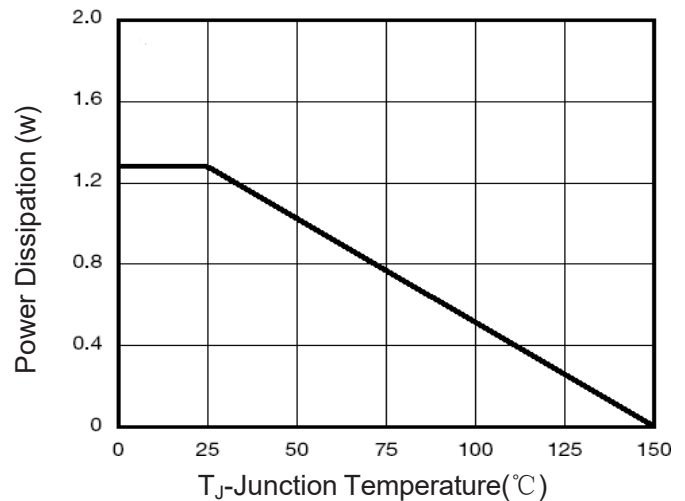
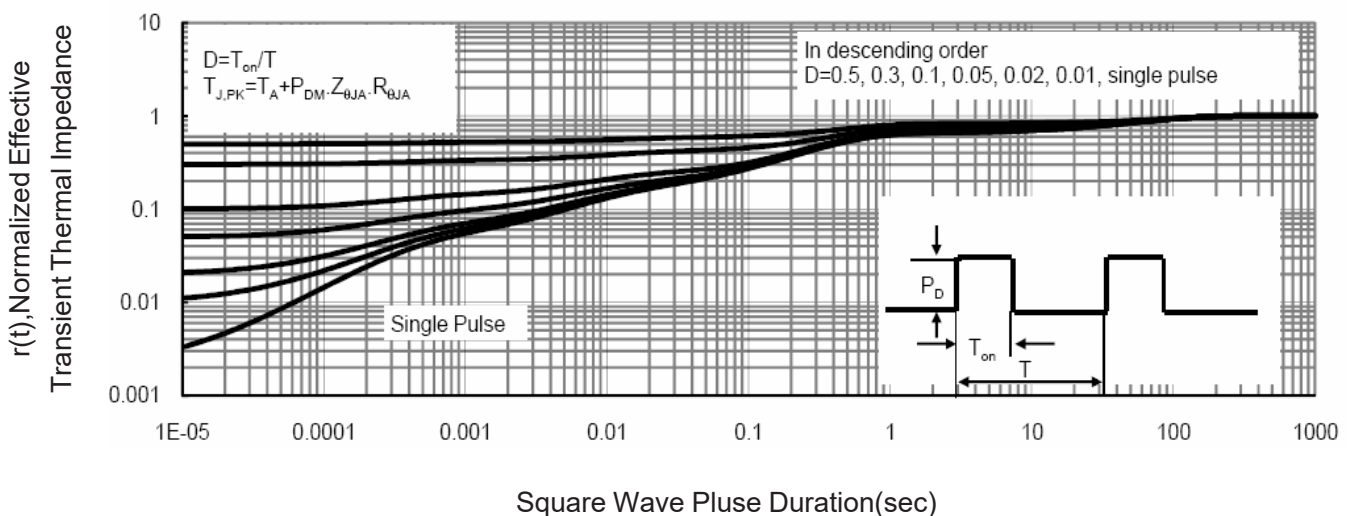


3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)


Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 Power De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance